•	•	•		
-,	1910	"semiconductor energy laboratory"	USPAT;	2003/02/08
'·	,		US-PGPUB;	16:01
	•		EPO; JPO;	1
			DERWENT;	
			IBM TDB	'
-	1910	"semiconductor energy laboratory"	USPAT;	2003/02/08
		·	US-PGPUB;	16:01
			EPO; JPO;	1
1	,		DERWENT;	·
4.4			IBM TDB	
	53714	barrier adj layer	USPAT;	2003/02/08
	2.54	Birman, the impositions made a statement making a section of the s	US-PGPUB;	16:02
			EPO; JPO;	
			DERWENT;	l l
	·		IBM_TDB	
-	65	"semiconductor energy laboratory" and	USPAT;	2003/02/08
	8	(barrier adj layer)	US-PGPUB;	16:24
			EPO; JPO;	·
			DERWENT;	
	*		IBM_TDB	
- '	3430	crystallization and (tft or thin adj film	USPAT;	2003/02/08
	1	adj transistor)	US-PGPUB;	16:26
			EPO; JPO;	
	I* :	*	DERWENT;	
	1.		IBM_TDB	
- '	318636	nickel	USPĀT;	2003/02/08
			US-PGPUB;	16:26
	1.		EPO; JPO;	
			DERWENT;	•
		*	IBM_TDB	
-	1134	(crystallization and (tft or thin adj	USPAT;	2003/02/08
· · · · · · · · · · · · · · · · · · ·		film adj transistor)) and nickel	US-PGPUB;	16:27
	1.		EPO; JPO;	1
]	* * *	DERWENT;	'
	1		IBM_TDB	
<u>-</u> .	6040	gettering	USPAT;	2003/02/08
	10		US-PGPUB;	16:27
		*	EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	369	((crystallization and (tft or thin adj	USPAT;	2003/02/08
	+	film adj transistor)) and nickel) and	US-PGPUB;	16:27
		gettering	EPO; JPO;	
9.5	1 .		DERWENT;	
			IBM_TDB	
	91222	silicon adj nitride	USPĀT;	2003/02/08
	1	•	US-PGPUB;	16:28
			EPO; JPO;	
1	1		DERWENT;	
,		111	IBM_TDB	2002/02/22
-	333		USPAT;	2003/02/08
	1	film adj transistor)) and nickel) and	US-PGPUB;	16:38
	1	gettering) and (silicon adj_nitride)	EPO; JPO;	
0	1		DERWENT;	
		l	IBM_TDB	0000 (00 (00
-	5036	Joo.in.	USPAT;	2003/02/08
	1		US-PGPUB;	16:38
			EPO; JPO;	·
			DERWENT;	
	47505	FEE AND	IBM_TDB	2002/02/00
_	47605	tft or thin adj film adj transistor	USPAT;	2003/02/08
e-		,	US-PGPUB;	16:39
	1		EPO; JPO;	
	1		DERWENT;]
		The sum and the sum of	IBM_TDB	2002/02/02
-	105	,	USPAT;	2003/02/08
		transistor)	US-PGPUB;	16:39
			EPO; JPO;	(X)
	1		DERWENT;	
	<u> </u>		IBM_TDB	l

-	13	(metal adj mask) and "t-shaped" and (co	USPAT;	2003/02/11
		or cobalt or ta or tantalum)	US-PGPUB;	11:11
•			EPO; JPO;	
		•	DERWENT;	
,		γ	IBM TDB	
_	2	"t-shaped" adj etching adj mask	USPĀT;	2003/07/18
			US-PGPUB;	10:26
			EPO; JPO;	-
			DERWENT;	
• . •	61 gr. 44	e e	IBM_TDB	
-	1	"5452164".PN.	USPAT	2003/07/18
	the stage comment of the	restriction of the second of t	- 1911 - William Company	10:28
	1	6303392.URPN.	USPAT	2003/07/18
				10:28
- ,	9	("4814258" "4859573" "4988609"	USPAT	2003/07/18
		"5468595" "5658469" "5725997"		10:32
•		"5885749" "6042975" "6303392").PN.		